

# IFE Materials Response RHEPP/MAP Materials Studies

November 14, 2001

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Sandia is a multiprogram laboratory operated by Sandia Corporation, a Lockheed Martin Company, for the United States Department of Energy under contract DE-AC04-94AL85000.

The MAP (Magnetically Confined Anode Plasma) Ion Source can generate multiple ion beams on RHEPP-



- 500-750 kV
- $\leq$  250 A/cm<sup>2</sup>
- Beams from H, He, N<sub>2</sub>, O<sub>2</sub>,
  Ne, Ar, Xe, and CH<sub>4</sub> gas
- Overall Treatment area

~ 100 cm<sup>2</sup>

• Diode vacuum ~ 10-<sup>5</sup> Torr

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- Beam composition posited, ٠ propagated to Fcup array using corrected diode voltage
- Composite compared to • averaged total Fcup signal
- 7 Fcups located 2 cm apart, for ٠ 25 < z < 63 cm
- Beam from 6 < r < 10 cm not ٠ counted (estimate 30% of total)



Simulated current

currer





#### He injection leads to long-lived pulse of pure He+1

700

Time (ns)

800





- Unlike Negeneration, current lags voltage, leading to debunching
- Current pulse width at 63 cm is • almost 0.5 µsec long
- Beam here was intentionally • attentuated



#### Proposed and tested samples for RHEPP

	Material	Fluence	Application
$\checkmark$	Graphite (Poco)	0.25-8 J/cm <sup>2</sup>	Dry wall
$\checkmark$	Tungsten	1-8 J/cm <sup>2</sup>	Dry wall
$\checkmark$	Tantalum	1-8 J/cm <sup>2</sup>	Dry wall
$\checkmark$	Carbon velvet	1-8 J/cm <sup>2</sup>	Dry wall
	Silicon Carbide		Dry wall
	Carbon Composite		Dry Wall
	Aluminum		Reference material





Poco subjected to 400 shots from He beam, Shows visible change down to 0.5 J/cm<sup>2</sup>





Interface, untreated Poco (bottom) and 0.25 - 0.5 J/cm<sup>2</sup> (top) - image 20x

Interface, untreated Poco (bottom) and 0.5 - 1 J/cm<sup>2</sup> (top) - image 20x



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'oco Graphite exposed to 5.5.J/cm<sup>2</sup> carbon/proton beam ablated at rate of 0.3 microns/pulse





- mechanically polished Poco graphite exposed to 75 pulses of 70% C/30% H beam at average dose of 5.5 J/cm<sup>2</sup>
- Profilometer scan across interface (left) shows ~ 20 micron step (0.27 µ/pulse)
- Ra (original) = 0.23 microns
- Ra (treated) = 3.6 microns



Ablation threshold appears to be 3 J/cm<sup>2</sup>, But surface roughening occurs down to below 1 J/cm<sup>2</sup>





- Mechanically polished Poco graphite exposed to 75 pulses of 70% C / 30% H beam at dose of 2 to 5.5 J/cm<sup>2</sup>
- Pre-treatment  $R_a \sim 0.1 0.2 \mu$
- $R_a$  (treated) as high as 3.6  $\mu$
- Step measurement accuracy
  ~ 0. 4 µ reached @ 3 J/cm<sup>2</sup>

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## Ta (and W) treated samples show roughening below the melt threshold





- Mechanically polished Ta exposed to 30 pulses of 70% C / 30% H beam at dose of 2 to 5.5 J/cm<sup>2</sup>
- Pre-treatment  $R_a < 0.1 \mu$
- R<sub>a</sub> (treated) roughly increases with dose
- Modeling shows surface temperature reaches ablation at ~ 3 J/cm<sup>2</sup>



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### Summary



- RHEPP/MAP can generate multiple ion beam species, in 500 kV pulses of ~ 0.5 µsec
- Ta/W shows increased roughness after treatment, but no discernable ablation, even at doses above vaporization



Velvet may represent a clear improvement over 1-d surface performance